

OptiMOS™-5 Power-Transistor



Features

- N-channel - Enhancement mode
- AEC qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green product (RoHS compliant)
- Ultra low Rds(on)
- 100% Avalanche tested

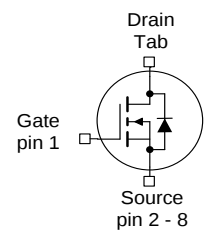
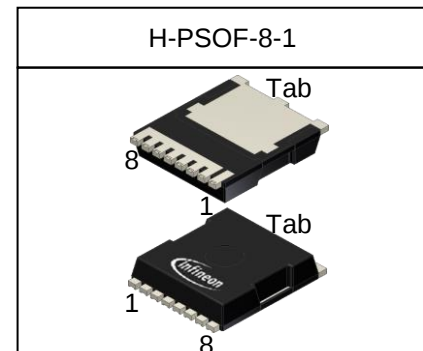
Type	Package	Marking
IAUT200N08S5N023	P/G-HSOF-8-1	5N08023

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$T_C=25\text{ °C}$, $V_{GS}=10\text{ V}^{1)}$	200	A
		$T_C=100\text{ °C}$, $V_{GS}=10\text{ V}^{2)}$	148	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_C=25\text{ °C}$	800	
Avalanche energy, single pulse ²⁾	E_{AS}	$I_D=100\text{ A}$	330	mJ
Avalanche current, single pulse	I_{AS}	-	200	A
Gate source voltage	V_{GS}	-	±20	V
Power dissipation	P_{tot}	$T_C=25\text{ °C}$	200	W
Operating and storage temperature	T_j, T_{stg}	-	-55 ... +175	°C
IEC climatic category; DIN IEC 68-1	-	-	55/175/56	

Product Summary

V_{DS}	80	V
$R_{DS(on)}$	2.3	mΩ
I_D	200	A



Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics²⁾

Thermal resistance, junction - case	R_{thJC}	-	-	-	0.7	K/W
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Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage ²⁾	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$	80	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=130\text{ }\mu\text{A}$	2.2	3	3.8	
Zero gate voltage drain current ²⁾	I_{DSS}	$V_{DS}=80\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$	-	0.1	1	μA
		$V_{DS}=40\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=85\text{ °C}^{2)}$	-	1	20	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=6\text{ V}$, $I_D=50\text{ A}$	-	2.7	3.7	$\text{m}\Omega$
		$V_{GS}=10\text{ V}$, $I_D=100\text{ A}$	-	1.8	2.3	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics²⁾

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=40\text{ V},$ $f=1\text{ MHz}$	-	5900	7670	pF
Output capacitance	C_{oss}		-	980	1274	
Reverse transfer capacitance	C_{rss}		-	45	68	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=40\text{ V}, V_{GS}=10\text{ V},$ $I_D=100\text{ A}, R_G=3.5\ \Omega$	-	16	-	ns
Rise time	t_r		-	11	-	
Turn-off delay time	$t_{d(off)}$		-	30	-	
Fall time	t_f		-	32	-	

Gate Charge Characteristics²⁾

Gate to source charge	Q_{gs}	$V_{DD}=40\text{ V}, I_D=100\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	28	36	nC
Gate to drain charge	Q_{gd}		-	18	28	
Gate charge total	Q_g		-	85	110	
Gate plateau voltage	$V_{plateau}$		-	4.8	-	V

Reverse Diode

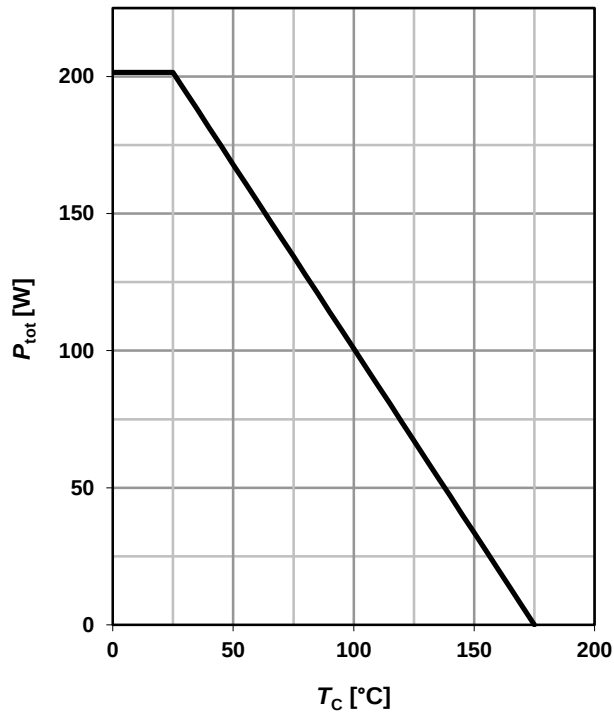
Diode continuous forward current ²⁾	I_S	$T_C=25\text{ °C}$	-	-	200	A
Diode pulse current ²⁾	$I_{S,pulse}$		-	-	800	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=100\text{ A},$ $T_J=25\text{ °C}$	-	0.9	1.2	V
Reverse recovery time ²⁾	t_{rr}	$V_R=40\text{ V}, I_F=50\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	65	-	ns
Reverse recovery charge ²⁾	Q_{rr}		-	110	-	nC

¹⁾ Current is limited by bondwire; with an $R_{thJC} = 0.7\text{ K/W}$ the chip is able to carry 216A at 25°C.

²⁾ Defined by design. Not subject to production test.

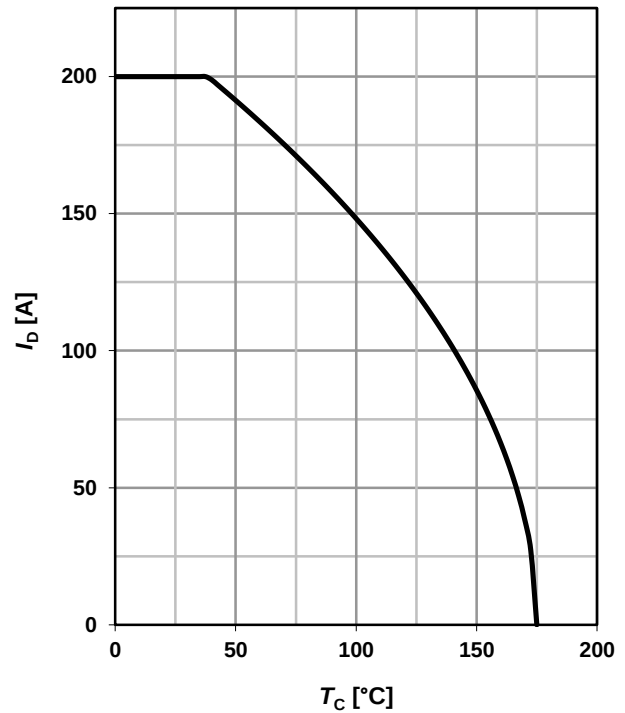
1 Power dissipation

$$P_{\text{tot}} = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$



2 Drain current

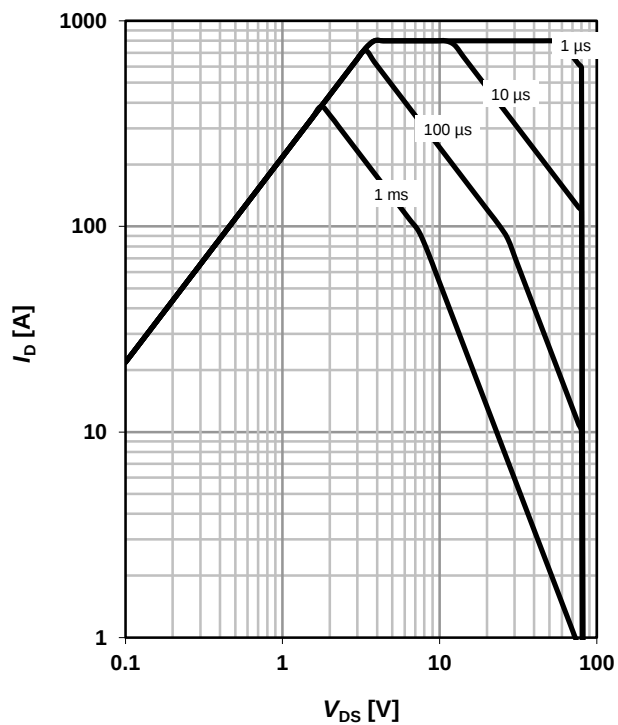
$$I_D = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$



3 Safe operating area

$$I_D = f(V_{\text{DS}}); T_C = 25^\circ\text{C}; D = 0$$

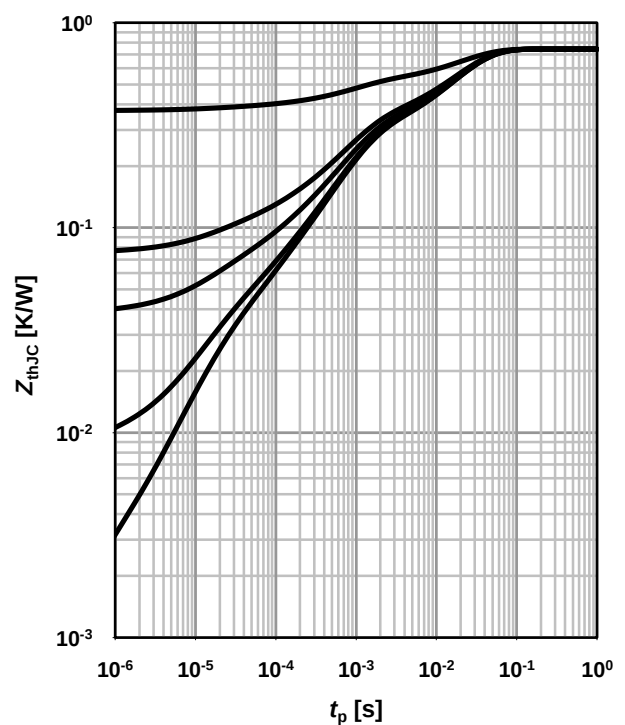
parameter: t_p



4 Max. transient thermal impedance

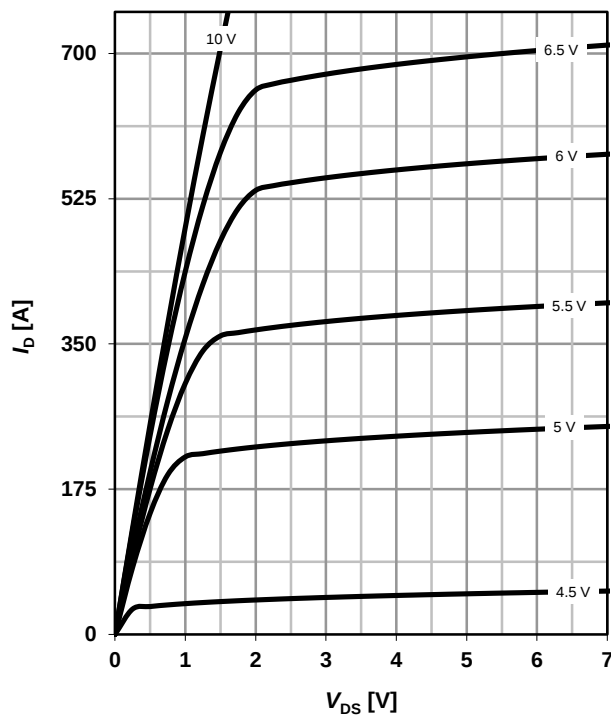
$$Z_{\text{thJC}} = f(t_p)$$

parameter: $D = t_p/T$



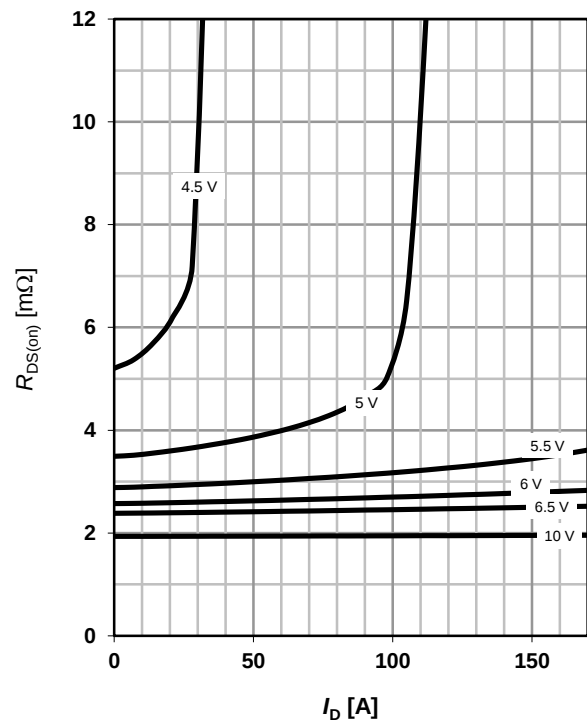
5 Typ. output characteristics

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

parameter: V_{GS}


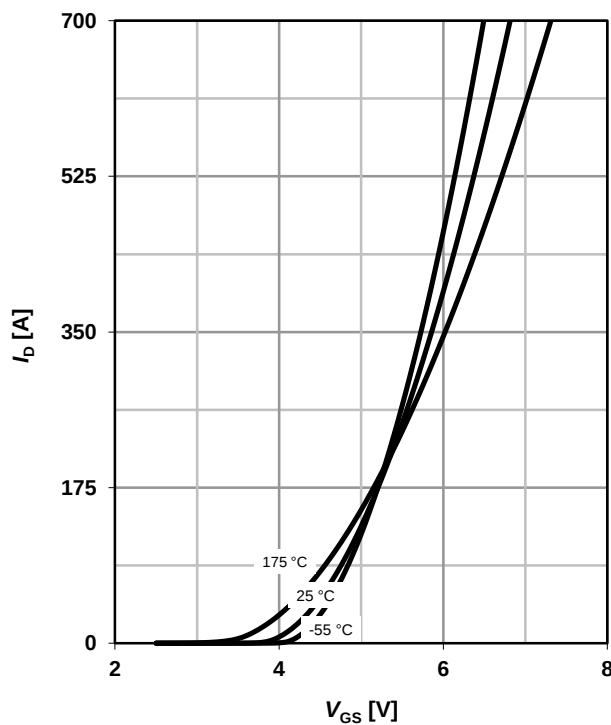
6 Typ. drain-source on-state resistance

 $R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$

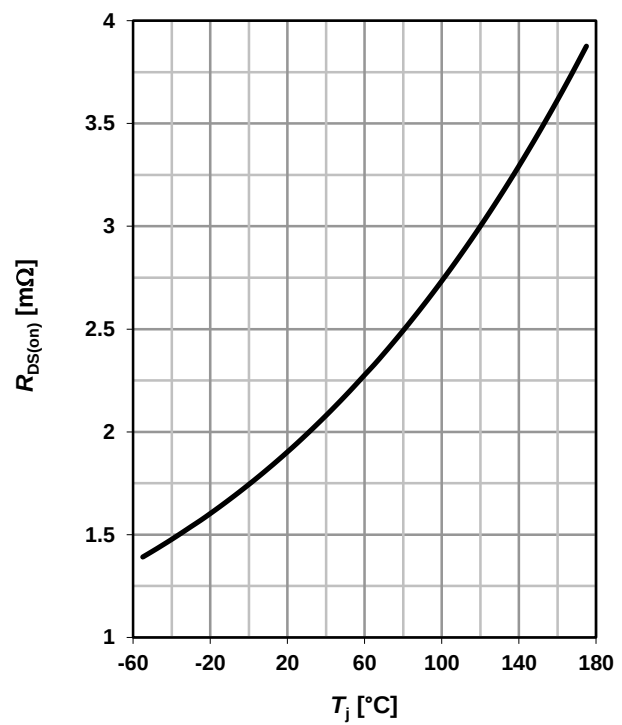
parameter: V_{GS}


7 Typ. transfer characteristics

 $I_D = f(V_{GS}); V_{DS} = 6\text{ V}$

parameter: T_j


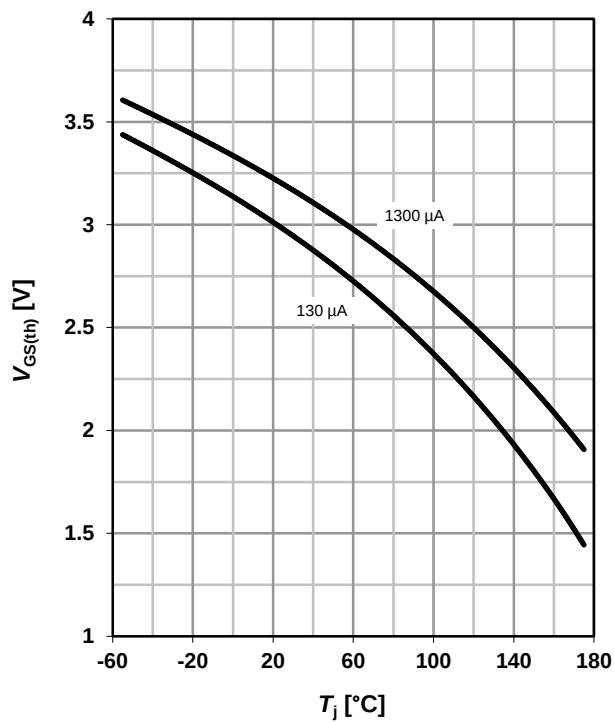
8 Typ. drain-source on-state resistance

 $R_{DS(on)} = f(T_j); I_D = 80\text{ A}; V_{GS} = 10\text{ V}$


9 Typ. gate threshold voltage

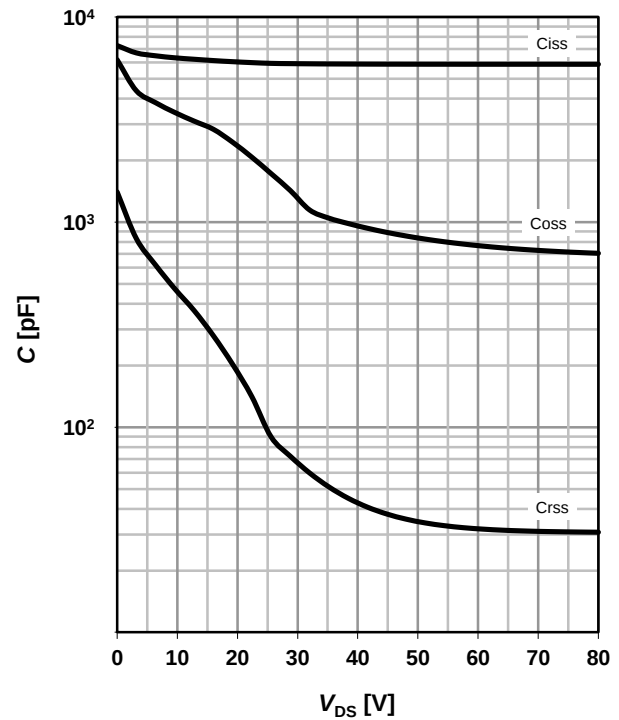
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

parameter: I_D



10 Typ. capacitances

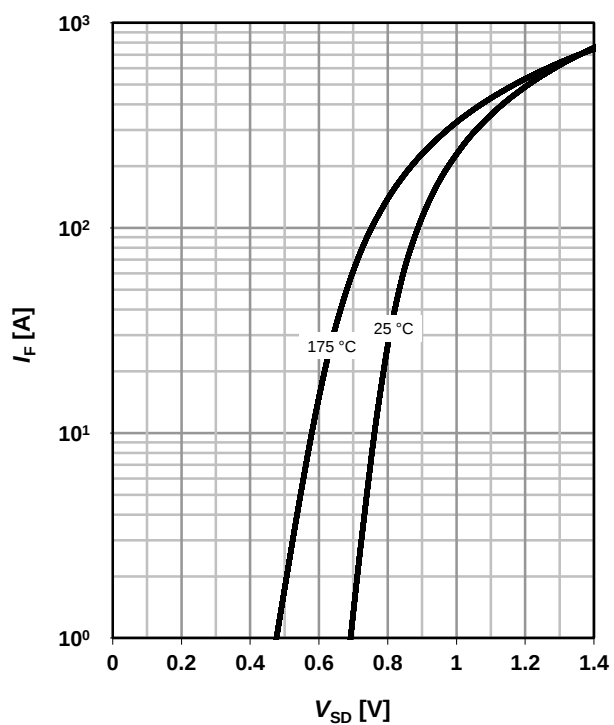
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$



11 Typical forward diode characteristics

$$I_F = f(V_{SD})$$

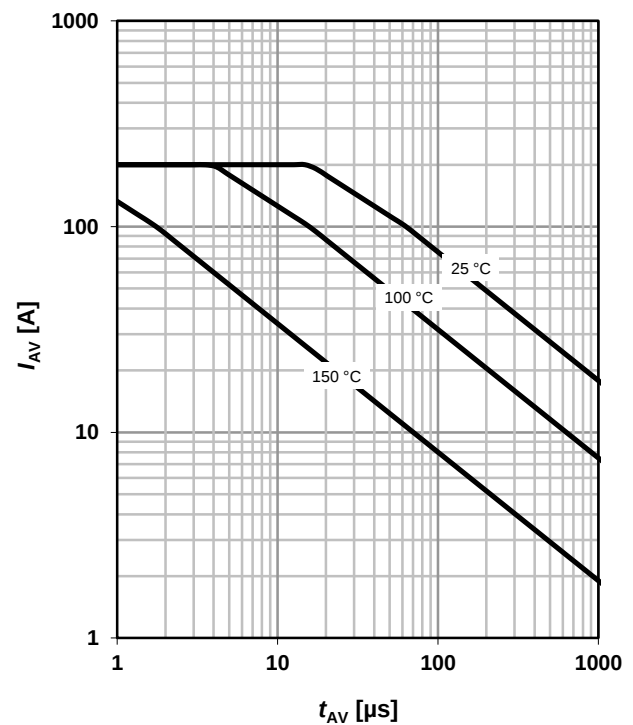
parameter: T_j



12 Typ. avalanche characteristics

$$I_{AS} = f(t_{AV})$$

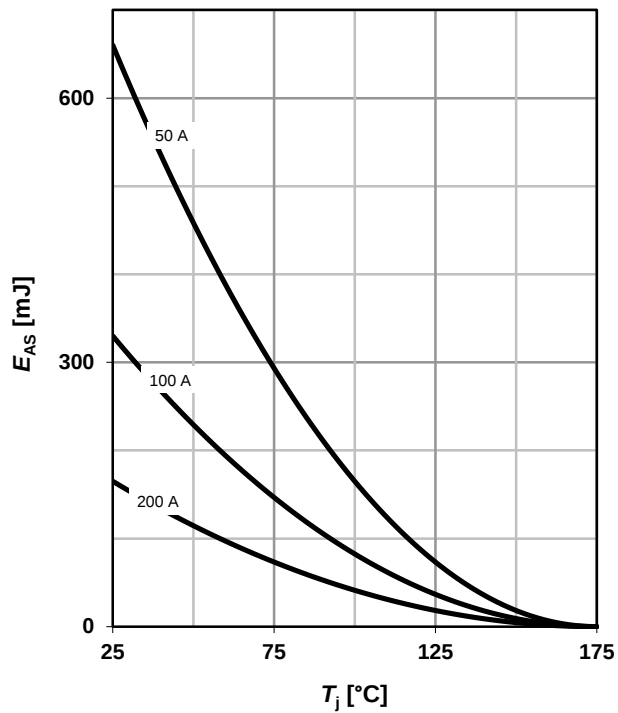
parameter: $T_{j(start)}$



13 Typical avalanche energy

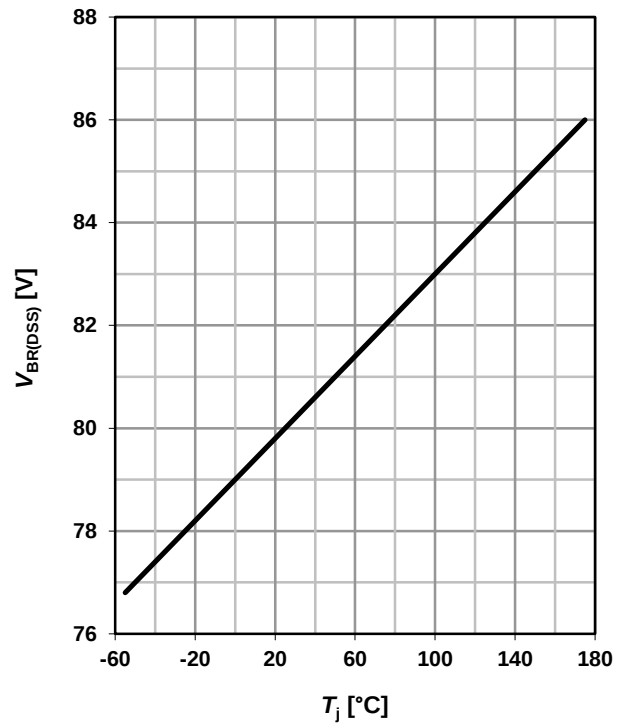
$$E_{AS} = f(T_j)$$

parameter: I_D



14 Drain-source breakdown voltage

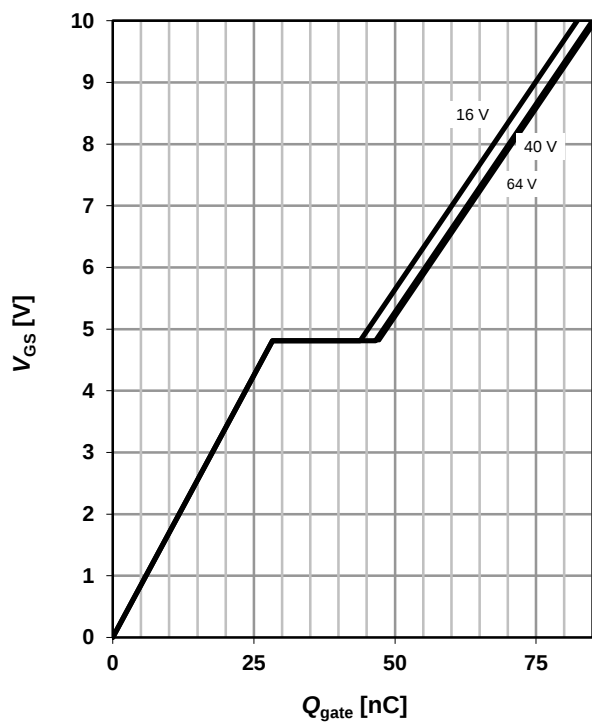
$$V_{BR(DSS)} = f(T_j); I_{D_typ} = 1 \text{ mA}$$



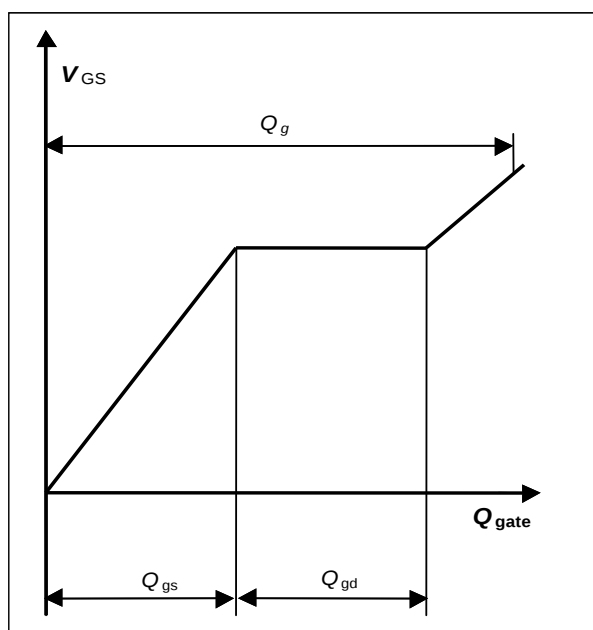
15 Typ. gate charge

$$V_{GS} = f(Q_{gate}); I_D = 100 \text{ A pulsed}$$

parameter: V_{DD}



16 Gate charge waveforms



Published by
Infineon Technologies AG
81726 Munich, Germany

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If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

Revision History

Version	Date	Changes
Version 1.0	15.12.2017	Final Data Sheet

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

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Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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